Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/640100	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 08:34
L2	2	("6777737").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 08:34
L11	4761	trench$3 near capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 08:53
L12	9784	vertical adj (transistor channel tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 08:53
L13	492	L11 and L12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 08:54
L14	108730	((dynamic adj random adj access adj memory) DRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 08:54
L15	462	l13 and L14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 08:54
L16	42	folded adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 08:55
L18	217	fold$3 adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 10:13

L19	0	l15 and l18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 08:55
L21	907	(257/302,305).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:15
L22	333	(348/242,243,386).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:16
L24	99	l21 and "l18"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:16
L25	43	l22 and "l18"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:16
L26	852108	gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:27
L27	18	l25 and L26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:27
L28	97	l24 and l26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:28
L29	67	l28 and gate near (electrode conduct$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:29
L30	4	l27 and gate near (electrode conduct$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:29

L31	53	29 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:44
L33	51	31 and (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:48
L34	15	33 and vertical adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:51
L35	8	34 and trench near capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:51
S1	1	10/604344	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:05
S2	1	trench near capacitor with folded near gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:07
S3	1	trench near capacitor same folded near gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:07
S4	2	trench near capacitor and folded near gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:14
S5	108588	((dynamic adj random adj access adj memory) DRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:16
S6	7	transistor near5 folded adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:17

S7	1	transistor with folded adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:17
S8	4	transistor same folded adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:18
S9	11	transistor and folded adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:19
S10	42	folded adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:19
S11	217	fold$3 adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:19
S12	25	transistor and fold$3 adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:20
S13	1	transistor and ((fold$3 adj gate) with (horizontal$3 and vertical$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:21
S14	5	((fold$3 adj gate) with (horizontal$3 and vertical$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 16:22
S15	2971	(257/301,313,532).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/11 16:22
S16	156	S15 and vertical$3 near transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/11 17:00

S17	4751	trench$3 near capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/11 17:00
S18	9776	vertical adj (transistor channel tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/11 17:01
S19	0	S17 and "I20"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/11 17:01
S20	491	S17 and S18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 08:53
S21	1635643	horizont$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/11 17:01
S22	2234218	vertical$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/11 17:02
S23	851380	gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 10:26
S24	86477	S21 and S22 and S23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/11 17:04
S25	9925	S21 with S22 with S23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/11 17:05
S26	16	S20 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/11 17:34

S27	82	alsmeier and siemens	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/11 17:34